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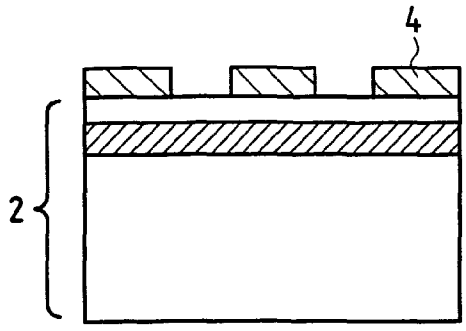
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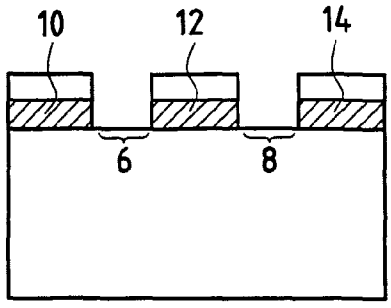
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(54) Title: SEMICONDUCTOR STRUCTURE, AND METHODS FOR FABRICATING SAME





(57) Abstract: The invention relates to a method of producing a semiconductor structure, the method comprising: - forming in a first semiconductor material substrate (30) a first dielectric area (32a-c) of a first dielectric material having a first thickness and a second dielectric area (34a-b) having a second thickness, - assembling said first substrate with a second semiconductor material substrate (40), - fracturing the portion of the substrate in which the weakened layer is produced, and- thinning one or both substrates.

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